L Number	Hits	Search Text	DB	Time stamp
1	21	(semiconductor near laser) and (active near (layer or region or	USPAT;	2002/06/18 11:31
		medium or film)) and (protection near (film or layer or region or	US-PGPUB;	
		medium)) and ridge and (refractive near (index or indice)) and	EPO; JPO;	
		(open\$5) and (shap\$4)	DERWENT;	
			IBM_TDB	
-	34	(semiconductor near laser) and (active near (layer or region or	USPAT;	2002/06/17 09:25
		medium or film)) and (protection near (film or layer or region or	US-PGPUB;	
		medium)) and ridge and (refractive near (index or indice))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	28	((semiconductor near laser) and (active near (layer or region or	USPAT;	2002/05/20 13:54
		medium or film)) and (protection near (film or layer or region or	US-PGPUB;	
		medium)) and ridge and (refractive near (index or indice))) and width	EPO; JPO;	
		width	DERWENT;	
	10	(semiconductor near locar) and ((active near flavor or negion or	IBM_TDB	0000/07/00 10 07
-	12	(semiconductor near laser) and ((active near (layer or region or	USPAT;	2002/05/20 10:37
		medium or film)) SAME (protection near (film or layer or region or medium)) SAME (SUBSTRATE)) and ridge and (refractive near	US-PGPUB; EPO; JPO;	
		(index or indice))	DERWENT;	
		(mack of marce))	IBM_TDB	
_	21	(semiconductor near laser) and ((active near (layer or region or	USPAT;	2002/05/20 15:02
	21	medium or film)) AND (protection near (film or layer or region or	US-PGPUB;	2002/03/20 13.02
		medium)) SAME (SUBSTRATE)) and ridge and (refractive near	EPO; JPO;	
		(index or indice))	DERWENT;	
1		(IBM_TDB	
-	17	((semiconductor near laser) and ((active near (layer or region or	USPAT;	2002/05/20 14:24
		medium or film)) AND (protection near (film or layer or region or	US-PGPUB;	
		medium)) SAME (SUBSTRATE)) and ridge and (refractive near	EPO; JPO;	
		(index or indice))) and width	DERWENT;	
			IBM_TDB	
-	10	((semiconductor near laser) and ((active near (layer or region or	USPAT;	2002/05/20 14:24
		medium or film)) SAME (protection near (film or layer or region	US-PGPUB;	
		or medium)) SAME (SUBSTRATE)) and ridge and (refractive near	EPO; JPO;	
		(index or indice))) and width	DERWENT;	
			IBM_TDB	
-	12	(semiconductor near laser) and ((active near (layer or region or	USPAT;	2002/05/20 16:36
		medium or film)) AND (protection near (film or layer or region or	US-PGPUB;	
		medium)) SAME (SUBSTRATE)) and (width same ridge) and	EPO; JPO;	
		(refractive near (index or indice))	DERWENT;	
		((comicon ductor man local) and ((c-time and)	IBM_TDB	0000/07/55 55
-	11	((semiconductor near laser) and ((active near (layer or region or	USPAT;	2002/05/21 08:26
		medium or film)) AND (protection near (film or layer or region or medium)) SAME (SUBSTRATE)) and (width same ridge) and	US-PGPUB;	
		(refractive near (index or indice)) and 372/\$	EPO; JPO; DERWENT;	
		(1011 about to hear (111 dice)) and 312/3	IBM_TDB	
_	456	(semiconductor near laser) and (active near (layer or region or	USPAT;	2002/05/21 10:56
1		medium or film)) and ((dielectric or insulat\$5 or protect\$5) near	US-PGPUB;	2002/ 00/ 21 10:00
		(film or layer or region or medium)) and ridge and (refractive near	EPO, JPO,	
		(index or indice))	DERWENT;	
		(IBM_TDB	
-	382	(semiconductor near laser) and (active near (layer or region or	USPAT;	2002/05/21 10:59
		medium or film)) and ((dielectric or insulat\$5 or protect\$5) near	US-PGPUB;	
		(film or layer or region or medium)) and ridge and (refractive near	EPO; JPO;	
		(index or indice)) AND substrate and width	DERWENT;	
		" "	IBM_TDB	
-	0	(semiconductor near laser) and (active near (layer or region or	USPAT;	2002/05/22 13:14
		medium or film)) and (((dielectric or insulat\$5 or protect\$5) near	US-PGPUB;	
		(film or layer or region or medium)) same substrat) and ridge and	EPO; JPO;	
Ī		(refractive near (index or indice)) and width	DERWENT;	
			IBM_TDB	

-	284	(semiconductor near laser) and (active near (layer or region or	USPAT;	2002/05/22 13:18
		medium or film)) and (((dielectric or insulat\$5 or protect\$5) near	US-PGPUB;	
		(film or layer or region or medium)) same substrate) and ridge and	EPO; JPO;	
		(refractive near (index or indice)) and width	DERWENT;	
			IBM_TDB	
-	131	(semiconductor near laser) and (active near (layer or region or	USPAT;	2002/05/22 13:21
		medium or film)) and (((dielectric or insulat\$5 or protect\$5) near	US-PGPUB;	
		(film or layer or region or medium)) same substrate same ridge) and	ЕРО; ЈРО;	
	İ	(refractive near (index or indice)) and width	DERWENT;	
			IBM_TDB	
-	29	(semiconductor near laser) and (active near (layer or region or	USPAT;	2002/05/22 14:31
		medium or film)) and (((dielectric or insulat\$5 or protect\$5) near	US-PGPUB;	
		(film or layer or region or medium)) same substrate same ridge same	EPO; JPO;	
		(refractive near (index or indice))) and width	DERWENT;	
			IBM_TDB	
-	23	((semiconductor near laser) and (active near (layer or region or	USPAT;	2002/05/22 14:31
		medium or film)) and (((dielectric or insulat\$5 or protect\$5) near	US-PGPUB;	
		(film or layer or region or medium)) same substrate same ridge same	EPO; JPO;	
		(refractive near (index or indice))) and width) and 372/\$	DERWENT;	!
		<i>""</i>	IBM_TDB	
_	6	((semiconductor near laser) and (active near (layer or region or	USPAT;	2002/05/22 14:32
		medium or film)) and (((dielectric or insulat\$5 or protect\$5) near	US-PGPUB;	
	1	(film or layer or region or medium)) same substrate same ridge same	EPO; JPO;	
		(refractive near (index or indice))) and width) and 257/\$	DERWENT;	
	i	(conductive near (masses))) and wramp and 20 % \$	IBM_TDB	
-	12	(semiconductor near device) and (active near (layer or region or	USPAT;	2002/05/22 14:36
		medium or film)) and (((dielectric or insulat\$5 or protect\$5) near	US-PGPUB;	2002/ 00/ 22 11.00
		(film or layer or region or medium)) same substrate same ridge same	EPO; JPO;	
		(refractive near (index or indice))) and width	DERWENT;	
		(remactive near (mack or matecy)) and within	IBM_TDB	
_	30	(semiconductor near (device or laser)) and (active near (layer or	USPAT;	2002/05/22 14:41
	"	region or medium or film)) and (((dielectric or insulat\$5 or	US-PGPUB;	2002/05/22 14.41
		protect\$5) near (film or layer or region or medium)) same substrate	EPO; JPO;	
		same ridge same (refractive near (index or indice))) and width	DERWENT;	
		same riage same (retractive near (mack or maice))) and wittin	IBM_TDB	
_	344	(semiconductor with optical) and substrate and (active near (layer or	USPAT;	2002/05/31 10:54
		film or region or medium)) and ((protect\$5 or insulat\$5) near (film	US-PGPUB;	2002/00/01 10.01
		or layer or region or medium)) and ridge and refractive	EPO; JPO;	
		or rayer or region or meanury) and ridge and refractive	DERWENT;	
	•		IBM_TDB	
_	114	(semiconductor with optical) and substrate and (active near (layer or	USPAT;	2002/05/31 13:23
	11.7	film or region or medium)) and ((protect\$5 or insulat\$5) near (film	US-PGPUB;	2002/03/31 13.23
		or layer or region or medium)) and (ridge or groove) and refractive	EPO; JPO;	
		and (stripe near shaped)	DERWENT;	
		and the hear maped	IBM_TDB	
_	o	((semiconductor with optical) and substrate and (active near (layer or	USPAT;	2002/05/31 13:33
		film or region or medium)) and ((protect\$5 or insulat\$5) near (film	US-PGPUB;	2002/00/01 10:00
		or layer or region or medium)) and (thickers or insulates) hear (film or layer or region or medium)) and (ridge or groove) and refractive	EPO; JPO;	
		and (stripe near shaped)) and (open\$5 near center) and (open\$5 near	DERWENT;	
		rear)	IBM_TDB	
_	108	((semiconductor with optical) and substrate and (active near (layer or	USPAT;	2002/05/31 13:38
	100	film or region or medium)) and ((protect\$5 or insulat\$5) near (film	US-PGPUB;	2002/00/31 13:38
		or layer or region or medium)) and (protects or insulats) near (inim	ЕРО; ЈРО;	
		and (stripe near shaped)) and width	DERWENT;	
		and (stripe near snaped)) and width		
_	90	(((semiconductor with optical) and substrate and (active near de-	IBM_TDB	0000/05/01 10 00
-	90	(((semiconductor with optical) and substrate and (active near (layer	USPAT;	2002/05/31 13:38
		or film or region or medium)) and ((protect\$5 or insulat\$5) near	US-PGPUB;	
		(film or layer or region or medium)) and (ridge or groove) and	EPO; JPO;	
		refractive and (stripe near shaped)) and width) and 372/\$	DERWENT;	
L			IBM_TDB	

-	27	(semiconductor near laser) and (active near (layer or region or	USPAT;	2002/06/18 11:28
		medium or film)) and (protection near (film or layer or region or	US-PGPUB;	
		medium)) and ridge and (refractive near (index or indice)) and	EPO; JPO;	
	ĺ	(open\$5)	DERWENT;	
			IBM TDB	